PUSHING LITHOGRAPHY TO ENABLE ULTIMATE NANO-ELECTRONICS

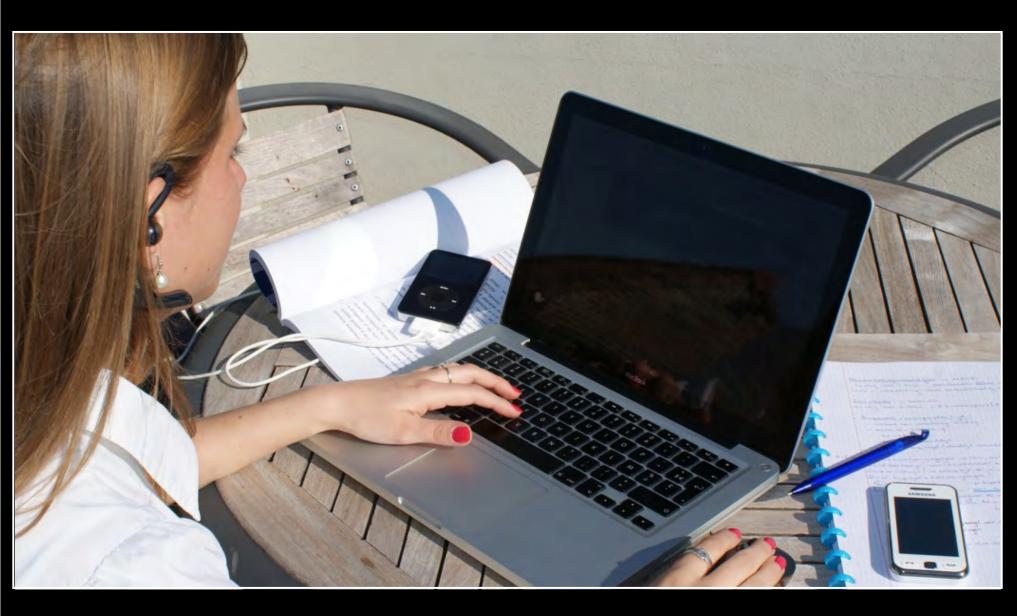
LUC VAN DEN HOVE

President & CEO imec





- Industry drivers
- Roadmap extension
- Lithography options
- Innovation through global collaboration









Experience the world wherever you are

Connected World

Computer Communication Consumer

Computer

Always connected Virtual Social Networks (Facebook, LinkedIn, Twitter, You Tube...)

Experience the world wherever you are

Ubiquitous Connectivity Video + Ultimate Graphics 30

Computing

Communication

Consumer

Computing

Communication

Consumer

Lifestyle Healthcare

BUSY LIFESTYLE

I billion overweight people300 million of those are obese

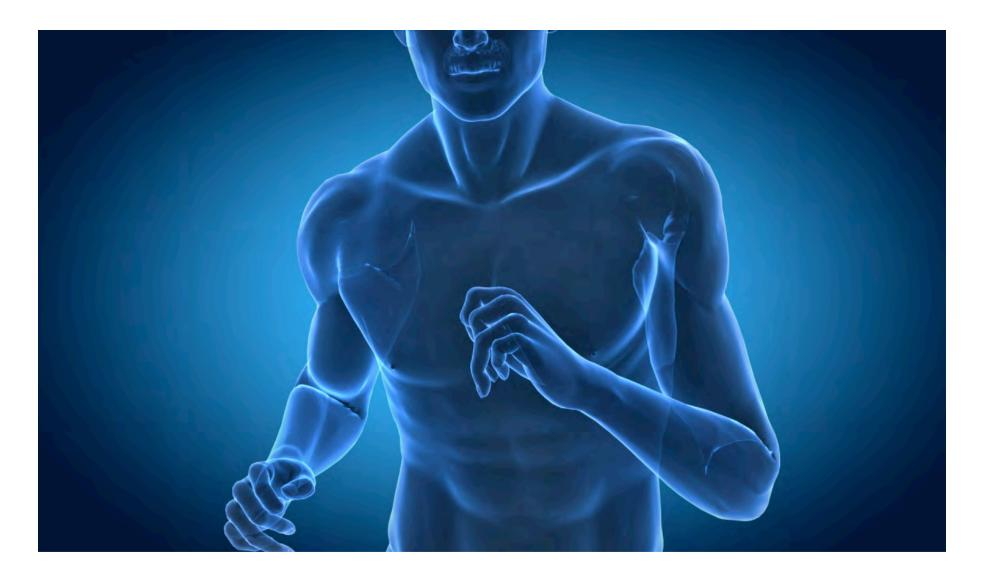
AGING POPULATION

600 million persons 60+ Expected to double by 2025

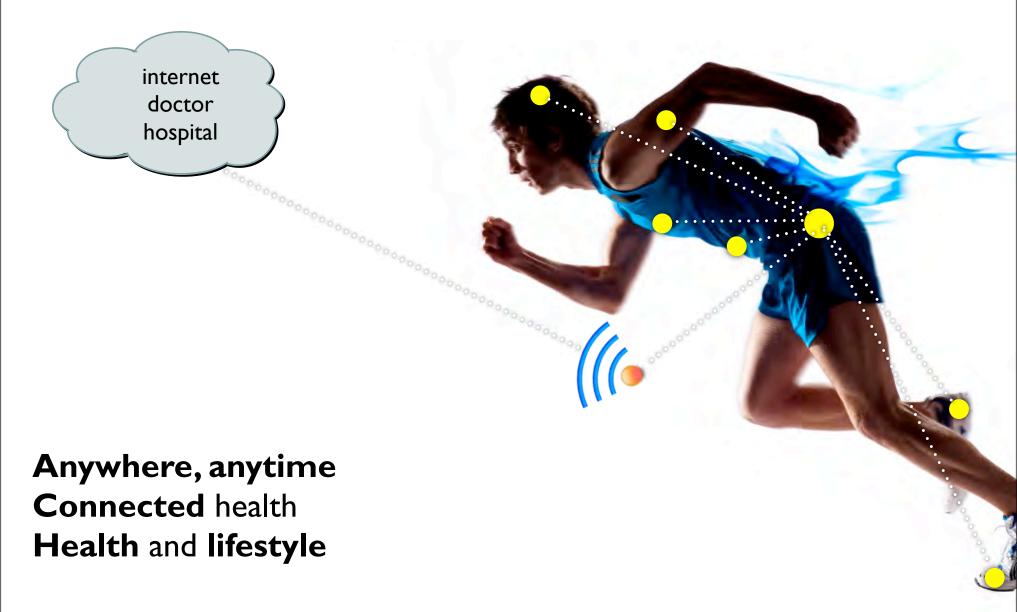
RISE IN CHRONIC DISEASES

600 million people worldwide\$500 billion a year (US)\$685 billion by 2020 (US)

MEDICINE GOES DIGITAL PERSONALIZED - PREDICTIVE - PREVENTIVE



WEARABLE HEALTH AND COMFORT MONITORING



WEARABLE HEALTH AND COMFORT MONITORING



ECG NECKLACE FOR AMBULATORY APPLICATIONS

WEARABLE HEALTH AND COMFORT MONITORING



























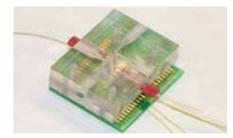




















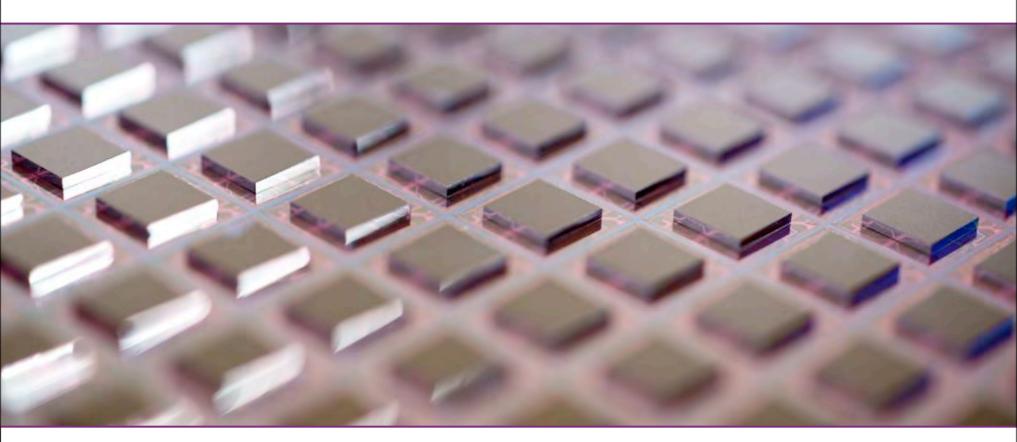






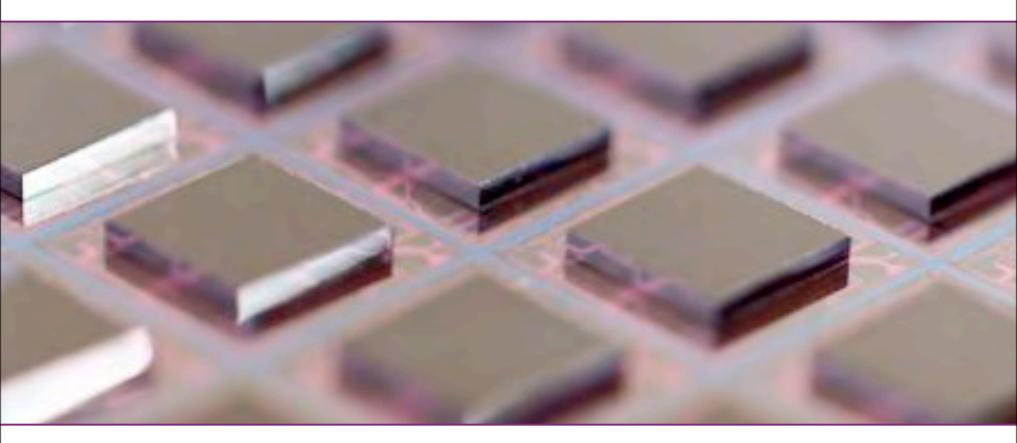


BOOSTING CHIP PERFORMANCE AND SYSTEM FUNCTIONALITY

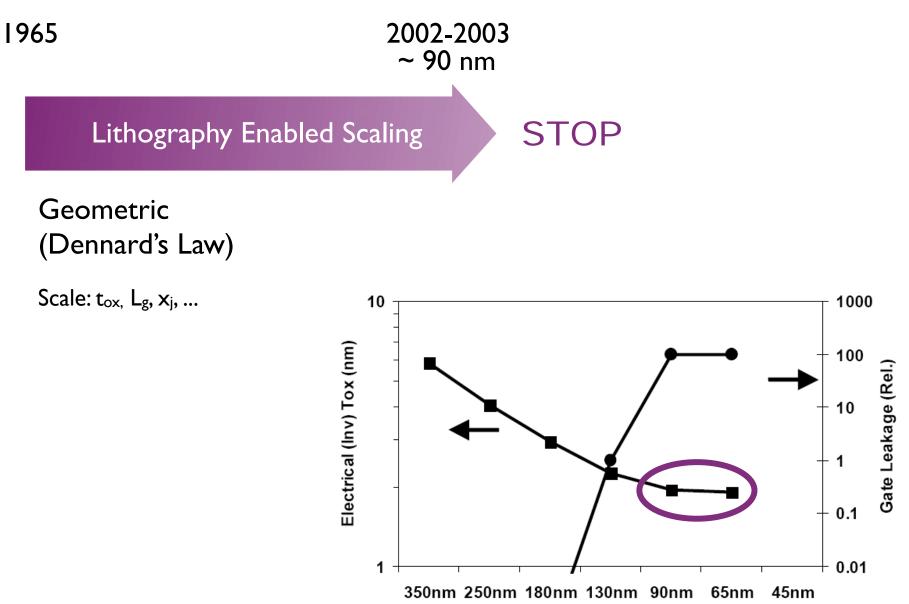


TERAFLOP TERABIT MORE FUNCTIONALITY

BOOSTING CHIP PERFORMANCE AND SYSTEM FUNCTIONALITY



TERAFLOP TERABIT MORE FUNCTIONALITY





2002-2003 ~ 90 nm

Lithography Enabled Scaling

Geometric (Dennard's Law)

Scale: $t_{ox,}$ L_g, x_j, ...

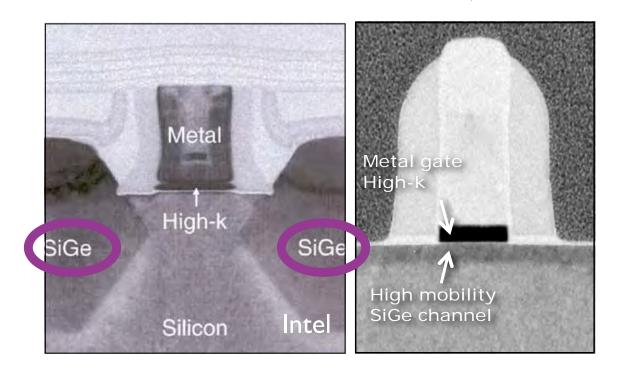
Materials Enabled Scaling

1965

2002-2003 ~ 90 nm

Lithography Enabled Scaling

Materials Enabled Scaling



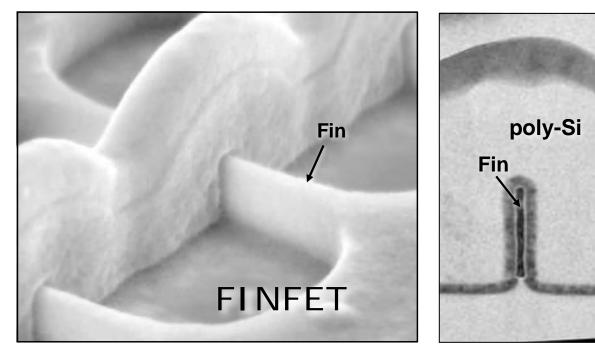
1965

2002-2003 ~ 90 nm

~ I5nm

Lithography Enabled Scaling

Materials Enabled Scaling



Strained Si High-k Metal Gate Multi Gate

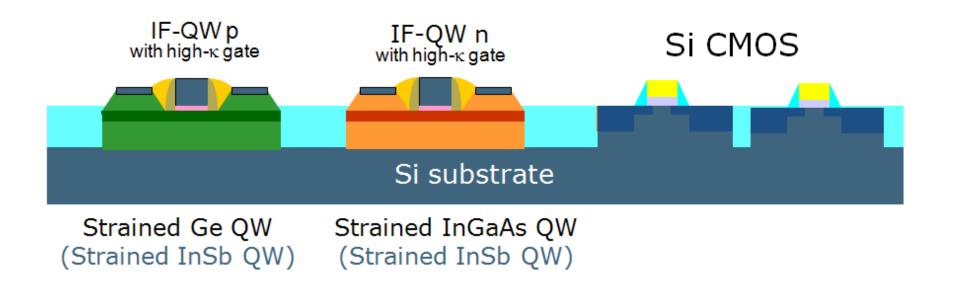


2002-2003 ~ 90 nm

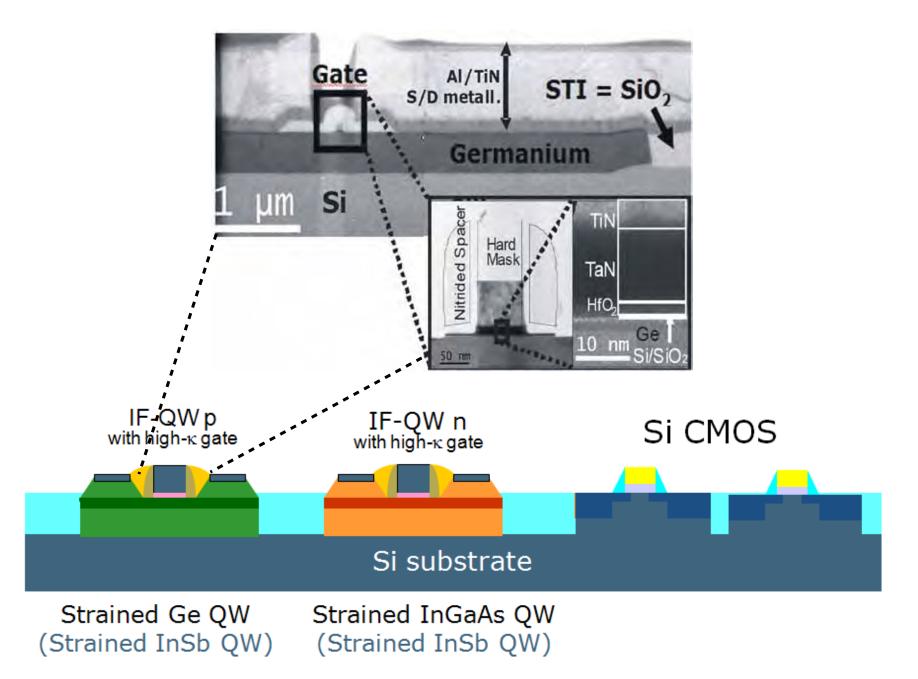
~ **I**5nm

Lithography Enabled Scaling

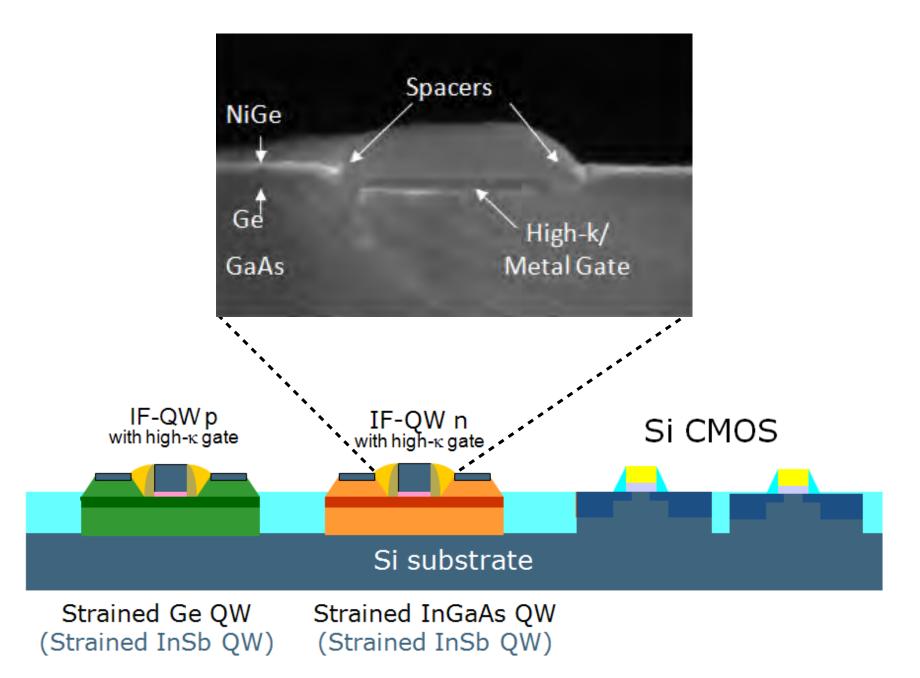
Materials Enabled Scaling



EXTREME HIGH MOBILITY CHANNELS



EXTREME HIGH MOBILITY CHANNELS



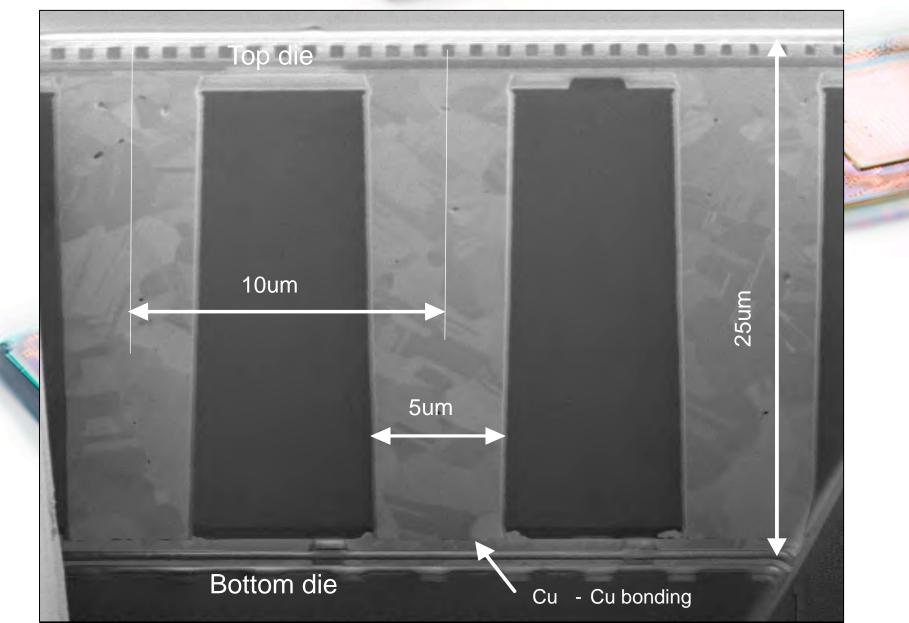
Lithography Enabled Scaling

Materials Enabled Scaling

3D Enabled Scaling

From Plane to Cube

3D STACKED ICS CONNECTED THROUGH TSVs



PERFORMANCE

MOBILE SYSTEMS

E.g., Netbooks

Cost, Power, Form factor, Performance

REUSE

COMPUTE SYSTEMS

E.g., Routers, Severs

Performance, Power efficiency, heat dissipation, Reliability 3D Integration & advanced packaging

CONSUMER

E.g., micro-servers

Power, Cost, Performance, Form factor, ...

MODULARITY

HEALTHCARE

E.g., sensor nodes

Form-factor, power, bio-compatibility, reliability

FORMFACTOR

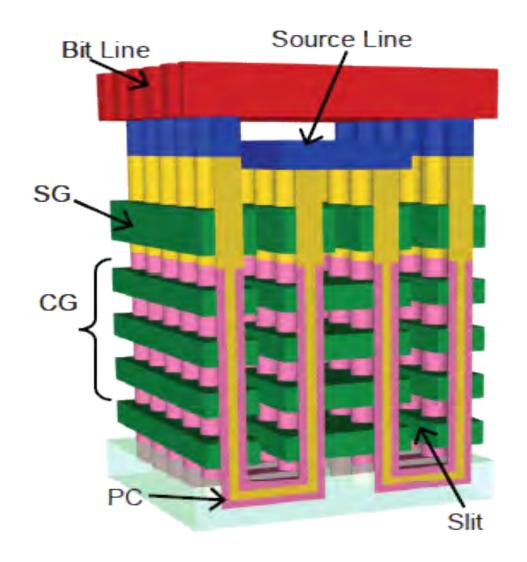
3D STACKED ICs CONNECTED THROUGH TSVs

Optical interconnects Photonics

Multi-core logic

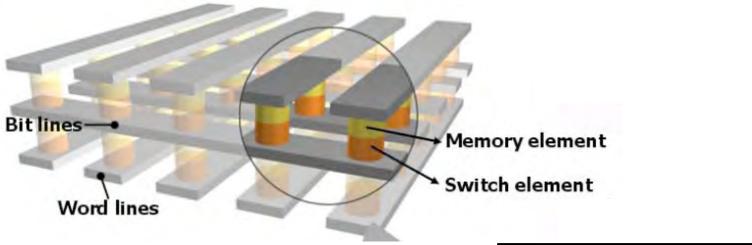
Memory

NEW MEMORY CONCEPTS

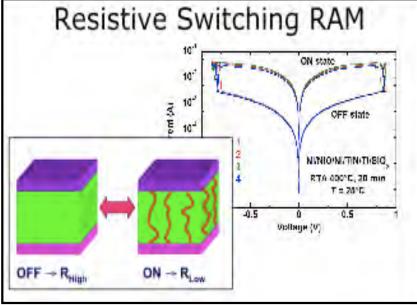


BiCS (ref. Toshiba)

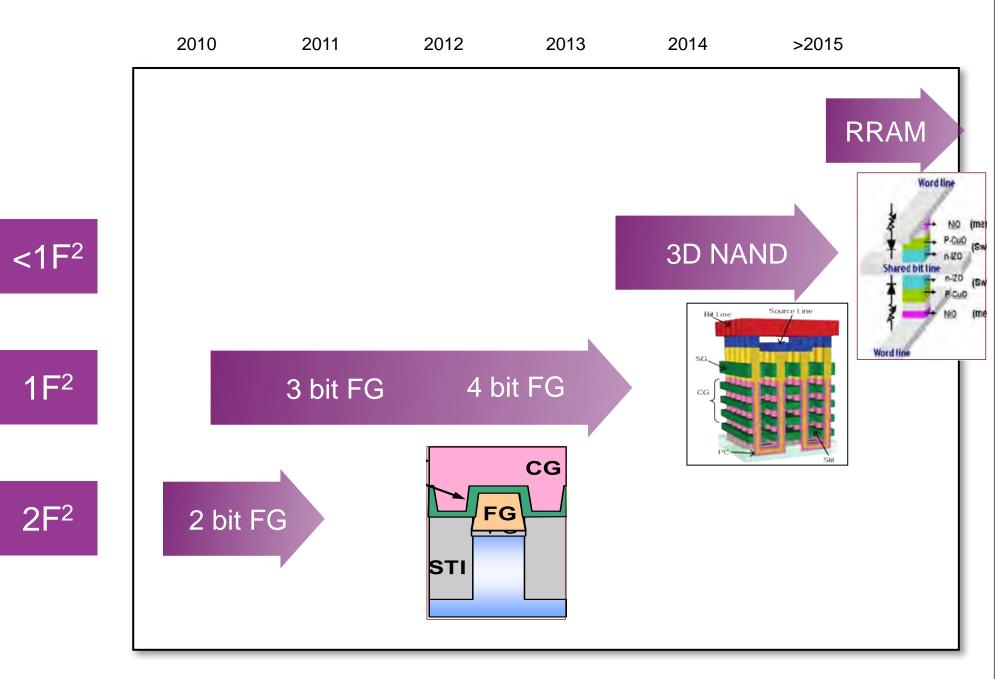
NEW MEMORY CONCEPTS



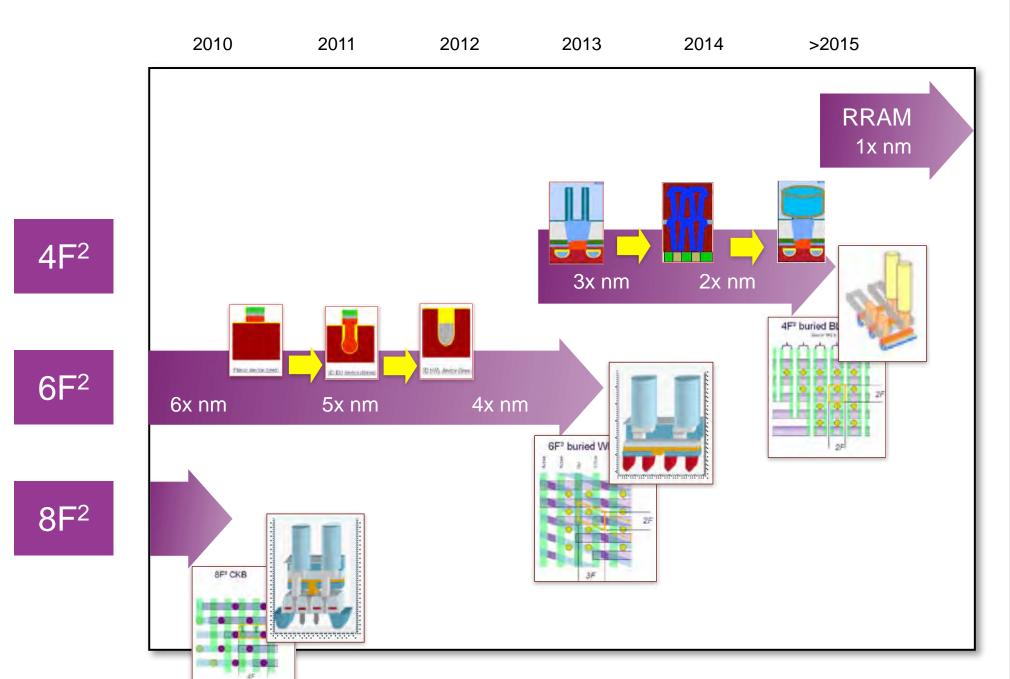
Cross-bar memory



LIKELY FLASH ROADMAP



LIKELY DRAM ROADMAP

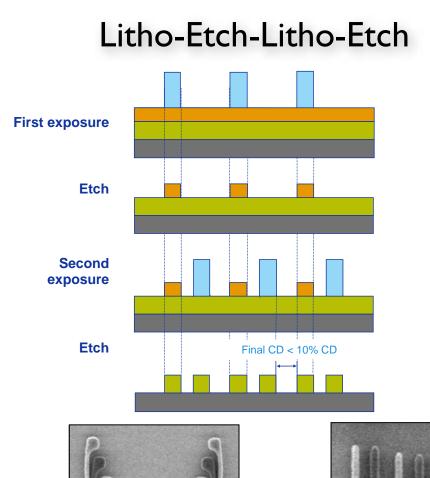


Lithography Enabled Scaling

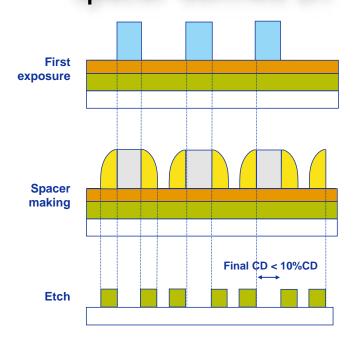
Materials Enabled Scaling

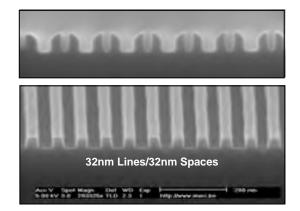
3D Enabled Scaling

DOUBLE PATTERNING

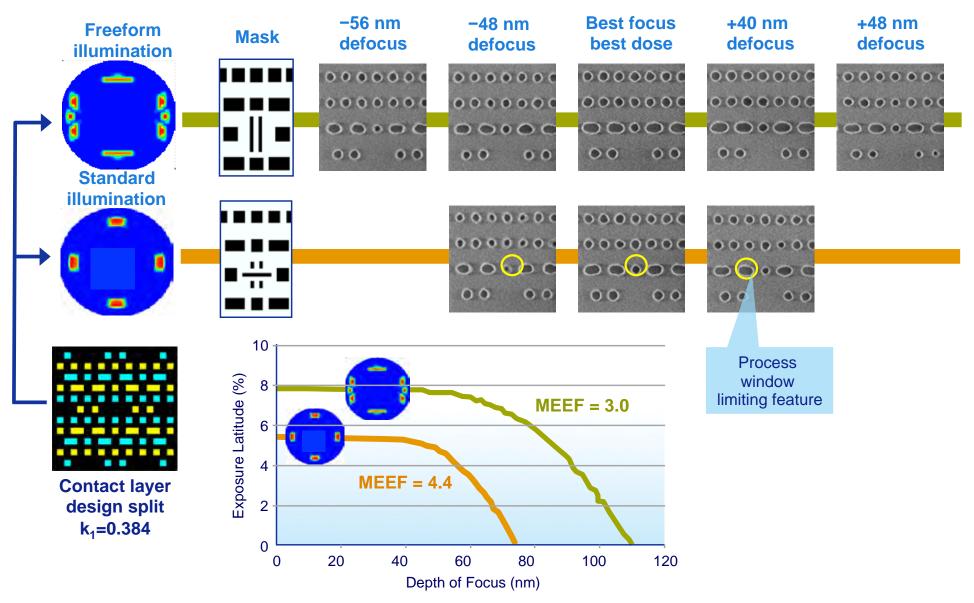


Spacer defined DP





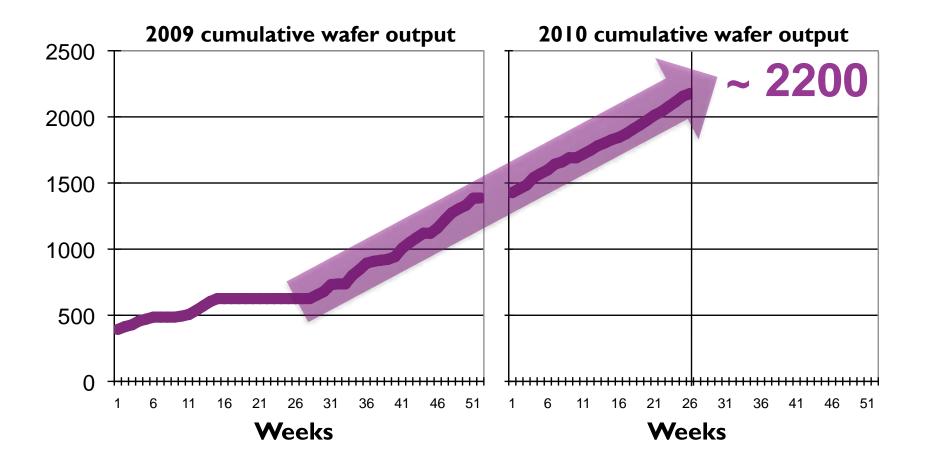
SOURCE MASK OPTIMIZATION 22NM SRAM PROCESS WINDOW WITH DOUBLE PATTERNING



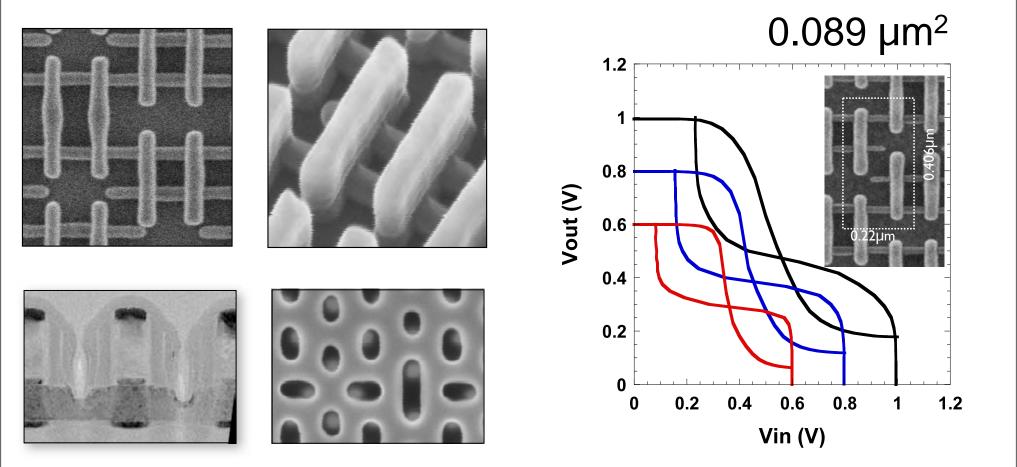
EUV LITHOGRAPHY



EUV TOOL OUTPUT



22nm NODE SRAM PATTERNING WITH EUV

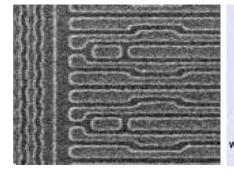


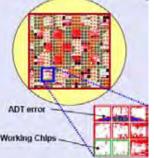
IMEC PARTNER EXPOSURES

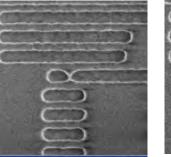


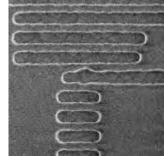






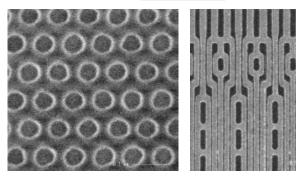


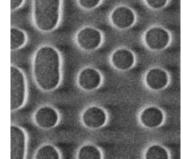


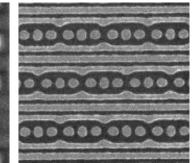




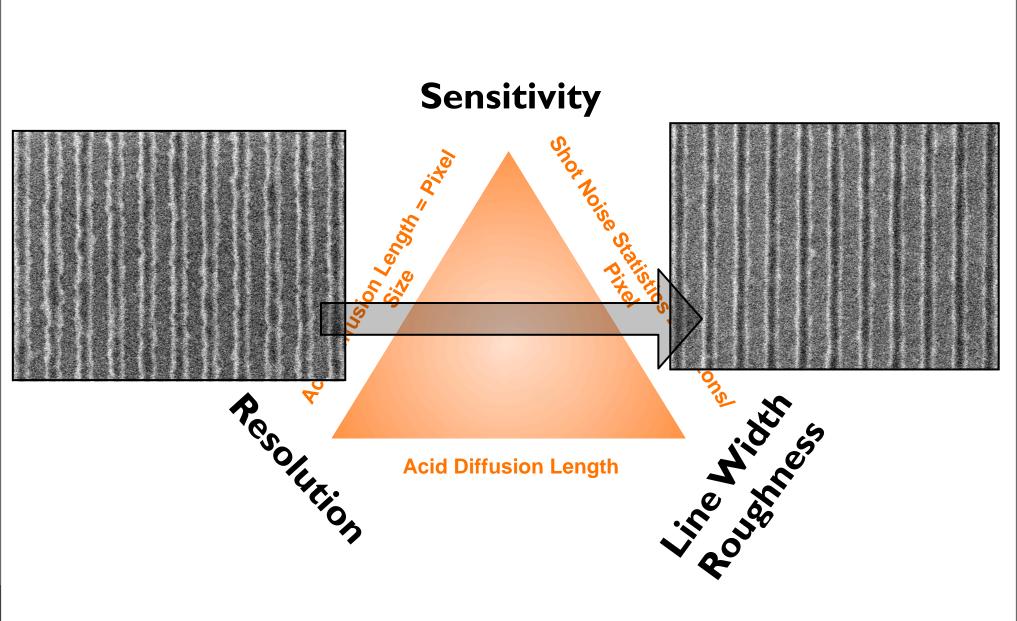




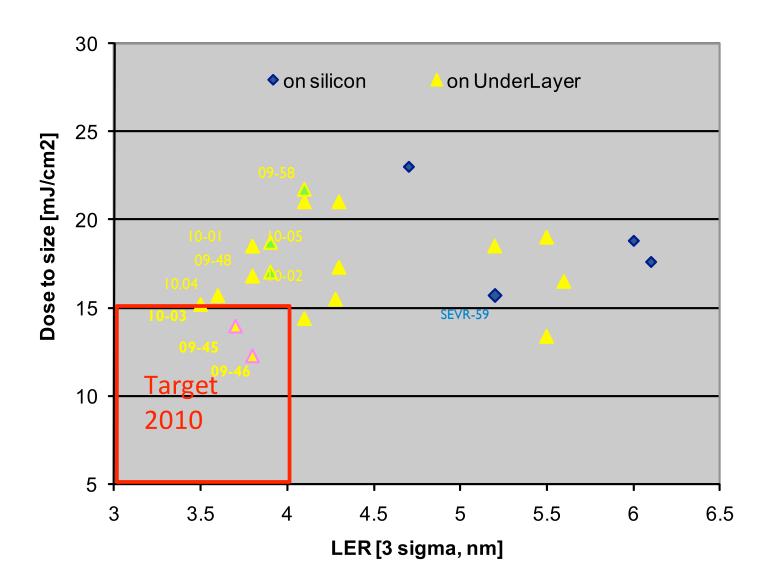




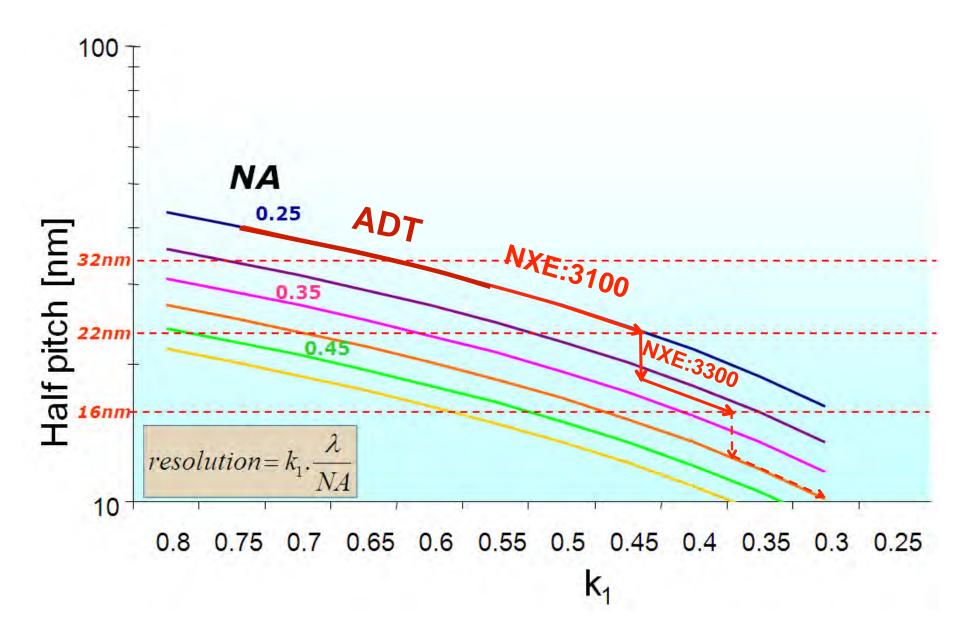
RESIST MATERIALS



RESIST MATERIALS



EUV ROADMAP TOWARDS 10nm



ML2 LITHO DEVELOPMENT

Meeting the 3 key targets (resolution, overlay, throughput) for direct write on Si is extremely challenging

Targets are rapidly moving according to Moore's law. Missing the targeted insertion node can have major impact on the ROI

Focusing on mask writing as intermediate milestone

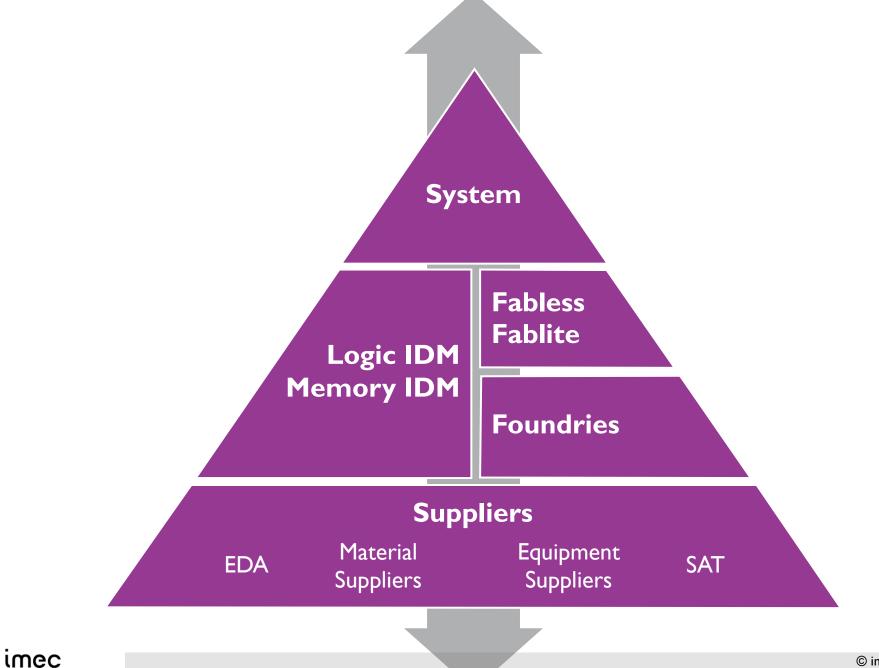
 Reduces the risk: any throughput improvement is welcome Both 193nm and EUVL can use this



- Industry drivers
- Roadmap extension
- Lithography options

Innovation through global collaboration

BRINGING TOGETHER FULL ECO SYSTEM



© imec 2010

BRINGING TOGETHER FULL ECO SYSTEM



CONCLUSIONS

Nano-electronics will continue to bring innovation into many converging application fields

Concurrent scaling enabled by

- lithography
- materials innovations
- 3D

Momentum on EUV has increased tremendously during last year

 Global collaboration (including entire value chain) is required to address the huge R&D challenges

ASPIRE INVENT ACHIEVE

